## What is claimed is:

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- 1. A method of forming an interconnect in a substrate which includes one or more dielectric layers and a copper deposit, said method comprising: forming a trench in the substrate; forming a via in the substrate to the copper deposit; depositing a layer of aluminum-0.5% copper alloy in the trench and via and on the copper deposit; depositing copper onto the aluminum-0.5% copper alloy; and polishing the copper.
- A method as recited in claim 1, wherein the step of depositing a
  layer of aluminum-0.5% copper alloy comprises depositing the aluminum-0.5% copper alloy using a PVD technique.
- A method of forming an interconnect in a substrate which includes one or more dielectric layers and a copper deposit, said method comprising:
  forming a trench in the substrate; forming a via in the substrate to the copper deposit; depositing an intermediate liner layer in the trench and via and on the copper deposit; depositing a layer of aluminum-0.5% copper alloy on the intermediate layer; and polishing the copper.

- 4. A method as recited in claim 3, wherein the step of depositing a layer of aluminum-0.5% copper alloy comprises depositing the aluminum-0.5% copper alloy using a PVD technique.
- 5. A method as recited in claim 3, wherein the step of depositing an intermediate liner layer comprises depositing Ta/TaN.
  - 6. An interconnect in a substrate which includes one or more dielectric layers, said interconnect comprising a first copper deposit, a second copper deposit, and an aluminum-0.5% copper alloy interconnect liner disposed between the first and second copper deposits and between the second copper deposit and at least one of the dielectric layers.

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7. An interconnect as recited in claim 6, wherein the aluminum-0.5% copper alloy interconnect liner has been deposited using a PVD technique.

8. An interconnect in a substrate which includes one or more dielectric layers, said interconnect comprising a first copper deposit, a second copper deposit, a intermediate interconnect liner disposed between the first and second copper deposits; and an aluminum-0.5% copper alloy interconnect liner disposed between the first and second copper deposits and between the second copper deposit and at least one of the dielectric layers.

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9. An interconnect as recited in claim 8, wherein the aluminum-0.5% copper alloy interconnect liner has been deposited using a PVD technique.

10. An interconnect as recited in claim 8, wherein the intermediate

interconnect liner comprises Ta/TaN.